

/ Descriptions

TO-220F N MOS N-CHANNEL MOSFET in a TO-220F Plastic Package.

/ Features

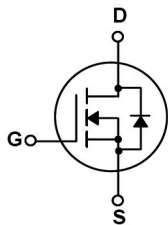
Low gate charge, low crss, fast switching.

/ Applications

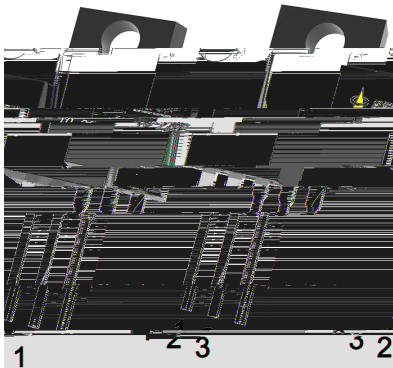
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

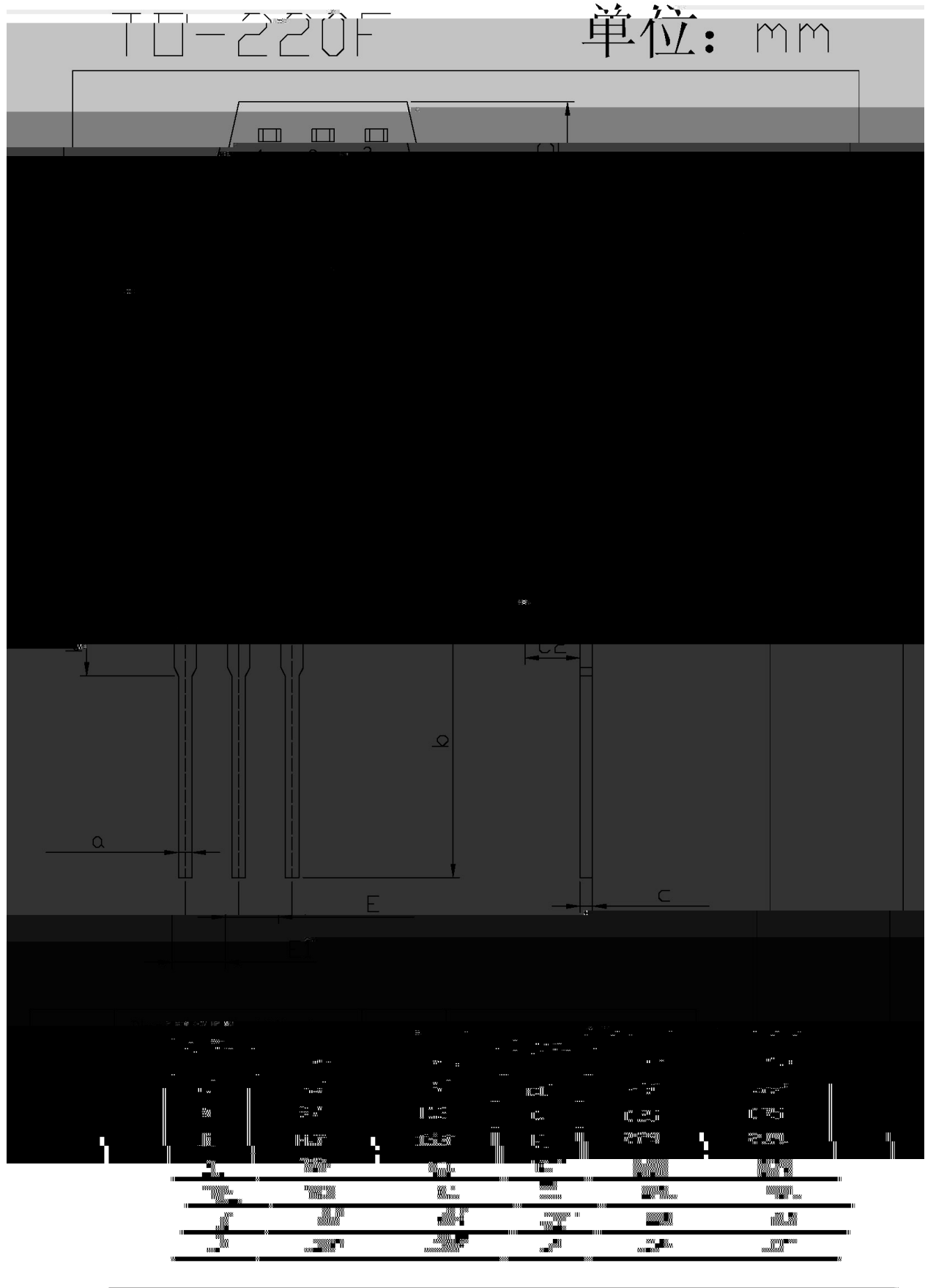
/ Marking

See Marking Instructions.

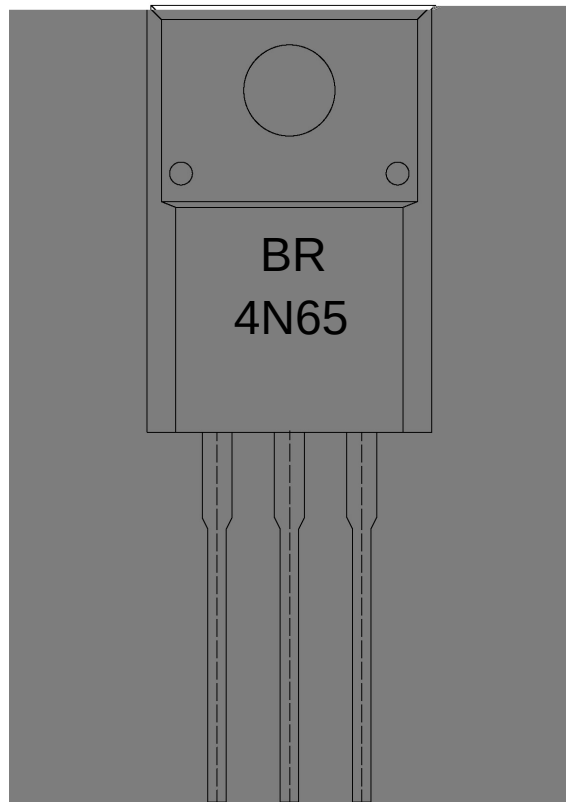
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	33	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu$				

/ Package Dimensions



/ Marking Instructions



BR

4N65

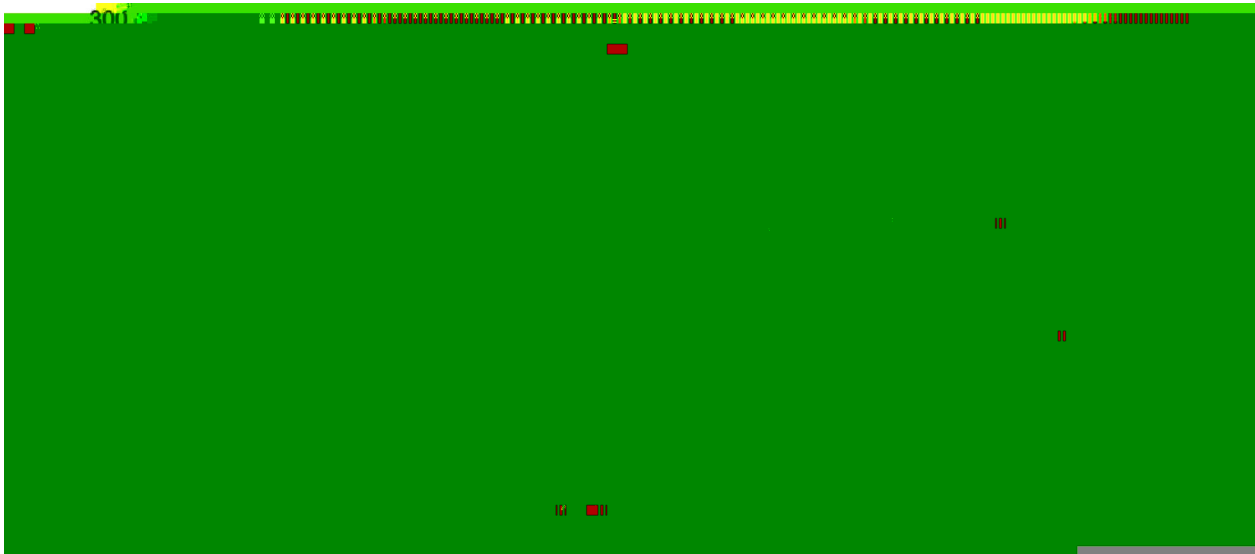
Note:

BR: Company Code

4N65: Product Type

****: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10 /sec.
- Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type

Units

Diment.01603bd×12